

Phase Control Thyristors, 175A

Features

- Improved glass passivation for high reliability
- Exceptional stability at high temperatures
- High di/dt and dv/dt capabilities
- Metric thread type available
- Low thermal resistance



TO-209AC (TO-93)

Voltage Ratings ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Type number	Voltage Code	V_{DRM}/V_{RRM} , Maximum repetitive peak and off-state voltage (V)	V_{RSM} , Maximum non-repetitive peak voltage (V)	I_{DRM}/I_{RRM} , Maximum at $T_J=T_J$ Maximum (mA)
175NT	20	200	300	30
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	
	160	1600	1700	

Electrical Ratings ($T_J = 25^\circ\text{C}$, unless otherwise noted)

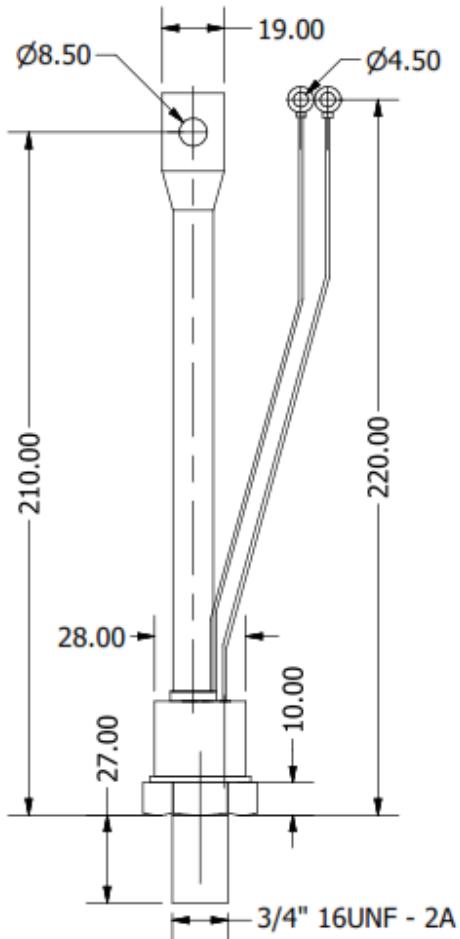
Parameters	Symbol	Values	Units
Maximum on-state average current	$I_{T(AV)}$	175	A
Maximum RMS on-state current	$I_{T(RMS)}$	275	A
Maximum peak, one cycle non-repetitive surge current	I_{TSM}	4700	A
Maximum I^2t for fusing	I^2t	110450	A^2s
Maximum peak on-state voltage	V_{TM}	1.75	V
Maximum holding current	I_H	300	mA
Maximum latching current	I_L	600	mA
Maximum rate of rise of turn-on current	di/dt	150	$\text{A}/\mu\text{s}$
Maximum critical rate of rise of off-state voltage	dv/dt	500	$\text{V}/\mu\text{s}$
Maximum gate current required to trigger	I_{GT}	200	mA
Maximum gate voltage required to trigger	V_{GT}	3	V

Thermal and Mechanical Specifications ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameters	Symbol	Values	Units
Maximum operating junction temperature range	T_J	- 40 to +125	$^\circ\text{C}$
Maximum storage temperature range	T_{Stg}	- 40 to +150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	$R_{th(JC)}$	0.11	$^\circ\text{C}/\text{W}$
Mounting torque $\pm 10\%$	F	30	Nm
Approximate weight	W	295	g

Package Outline

(All dimensions in mm)



Ordering Table

175	NT	120
1	2	3

1 – Current Rating = $I_F (AV)$

2 – Phase Controlled Thyristor (SCR)

3 – Voltage $\times 10 = V_{RRM}$